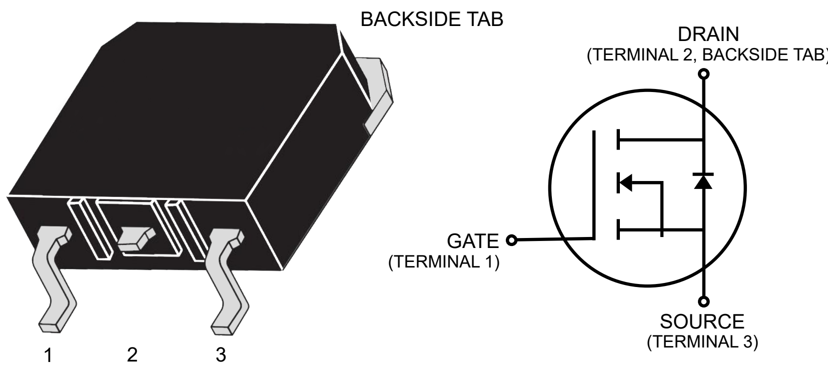
700V, 15 mΩ N-Channel mSiC™ MOSFET

MSC015SMA070S

Product Overview

700V, 15 mΩ typical at V_{GS} = 20V, 17 mΩ typical at V_{GS} = 18V, Silicon Carbide (SiC) N-Channel MOSFET, D3PAK (TO-268).



Features

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{J(max)}$ = 175 °C
- Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant

Benefits

- High efficiency to enable lighter and more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

Applications

- Photovoltaic (PV) inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- Hybrid Electric Vehicle (HEV) powertrain and Electric Vehicle (EV) charger
- Power supply and distribution

1. Device Specifications

This section shows the specifications of this device.

1.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of this device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain source voltage	700	V
I_D	Continuous drain current at T_C = 25 °C	112	A
	Continuous drain current at T_C = 100 °C	94	
I_{DM}	Pulsed drain current[1]	450	
V_{GS}	Gate-source voltage	23 to –10	V
	Transient gate-source voltage	25 to –12	
P_D	Total power dissipation at T_C = 25 °C	477	W
	Linear derating factor	3.2	W/°C

Note:

1. Repetitive rating: pulse width and case temperature are limited by the maximum junction temperature.

The following table shows the thermal and mechanical characteristics of this device.

Table 1-2. Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance	—	0.24	0.31	°C/W
T_J	Operating junction temperature	–55	—	175	°C
T_{STG}	Storage temperature	–55	—	150	°C
—	Reflow temperature	—	—	260	°C
Wt	Package weight	—	4.0	—	g

ESD practices should comply with JESD-625.

1.2 Electrical Performance

The following table shows the static characteristics of this device. T_J = 25 °C unless otherwise specified.

Table 1-3. Static Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0V, I_D = 100 µA	700	—	—	V
$R_{DS(on)}$	Drain-source on resistance[1]	V_{GS} = 20V, I_D = 40A	—	15	19	mΩ
		V_{GS} = 18V, I_D = 40A	—	17	—	
$V_{GS(th)}$	Gate-source threshold voltage	V_{GS} = V_{DS}, I_D = 4 mA	1.9	3.0	5.0	V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 700V, V_{GS} = 0V	—	0.3	35	µA
		V_{DS} = 700V, V_{GS} = 0V, T_J = 175 °C	—	3.5	—	
I_{GSS}	Gate-source leakage current	V_{GS} = 20V/–10V	—	—	±100	nA

Note:

1. Pulse test: pulse width < 380 µs, duty cycle < 2%.

The following table shows the dynamic characteristics of this device. T_J = 25 °C unless otherwise specified. The dynamic characteristics are characterized, not 100% tested, at the recommended operating V_{GS} = 20V/–5V.

Table 1-4. Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0V V_{DD} = 700V V_{AC} = 25 mV ƒ = 200 kHz	—	4324	—	pF
C_{rss}	Reverse transfer capacitance		—	44	—	
C_{oss}	Output capacitance		—	506	—	
Q_G	Total gate charge	V_{GS} = –5V/20V V_{DD} = 470V I_D = 40A	—	215	—	nC
Q_{GS}	Gate-source charge		—	58	—	
Q_{GD}	Gate-drain charge		—	35	—	
$t_{d(on)}$	Turn-on delay time	V_{DD} = 470V V_{GS} = –5V/20V I_D = 50A $R_{G(ext)}$ = 4Ω Freewheeling diode = MSC015SMA070S (V_{GS} = –5V); reference Figure 1-18	—	25	—	ns
t_r	Voltage rise time		—	34	—	
$t_{d(off)}$	Turn-off delay time		—	53	—	
t_f	Voltage fall time		—	20	—	
E_{on}	Turn-on switching energy		—	856	—	µJ
E_{off}	Turn-off switching energy		—	129	—	
ESR	Gate equivalent series resistance	f = 1 MHz, 25 mV, drain short	—	0.69	—	Ω
SCWT	Short circuit withstand time	V_{DS} = 560V, V_{GS} = 20V	—	3.0	—	µs
E_{AS}	Avalanche energy, single pulse	I_D = 40A	—	6400	—	mJ

The following table shows the body diode characteristics of this device. T_J = 25 °C unless otherwise specified. The body diode reverse recovery is characterized, not 100% tested.

Table 1-5. Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	I_{SD} = 40A, V_{GS} = 0V	—	3.3	—	V
		I_{SD} = 40A, V_{GS} = –5V	—	3.6	5.0	
t_{rr}	Reverse recovery time	I_{SD} = 50A, V_{GS} = –5V, Drive R_G = 4Ω, V_{DD} = 470V, dI/dt = –6800 A/µs	—	37	—	ns
Q_{rr}	Reverse recovery charge		—	631	—	nC
I_{RRM}	Reverse recovery current		—	68	—	A

1.3 Typical Performance Curves

Data for performance curves are characterized, not 100% tested.

Figure 1-1. Drain Current vs. V_{DS} at T_J

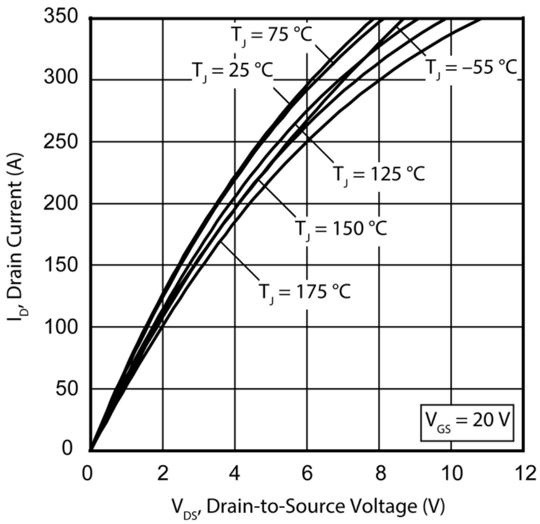


Figure 1-2. Drain Current vs. V_{DS} at V_{GS}

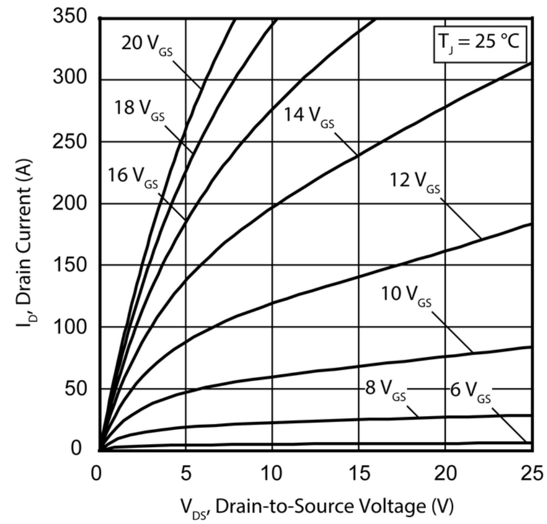


Figure 1-3. Drain Current vs. V_{DS} at V_{GS}

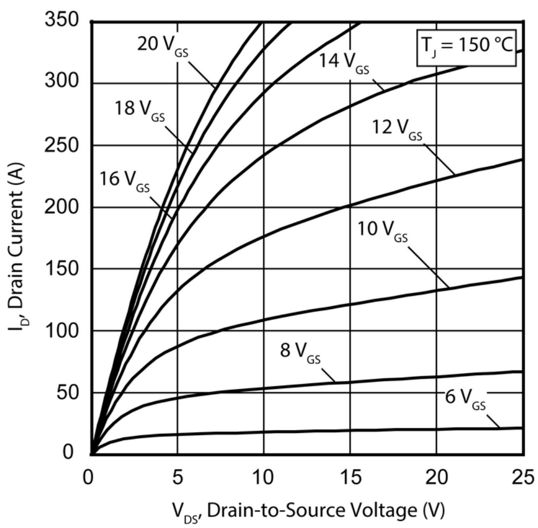


Figure 1-4. Drain Current vs. V_{DS} at V_{GS}

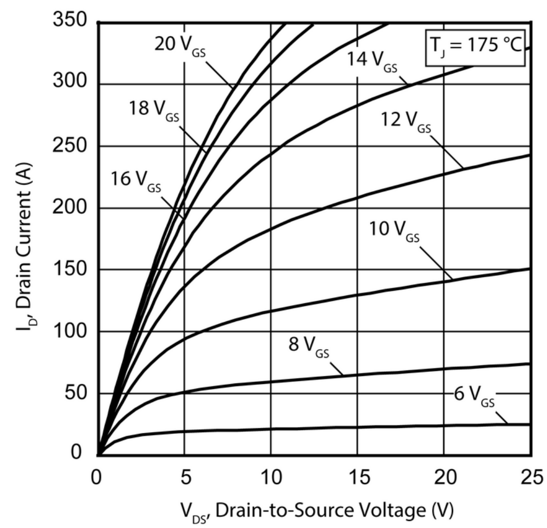


Figure 1-5. $R_{DS(on)}$ vs. Junction Temperature

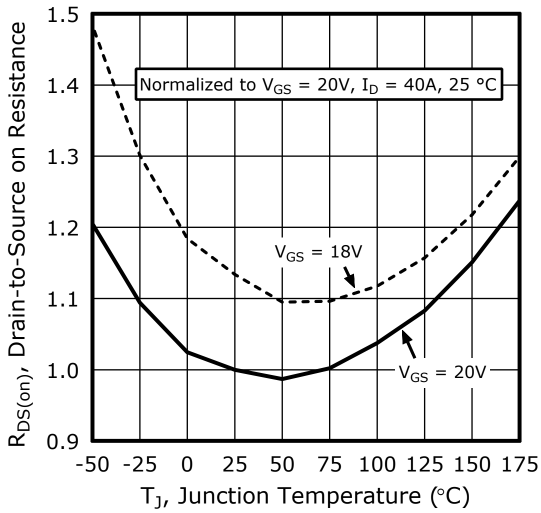


Figure 1-6. Gate Charge Characteristics

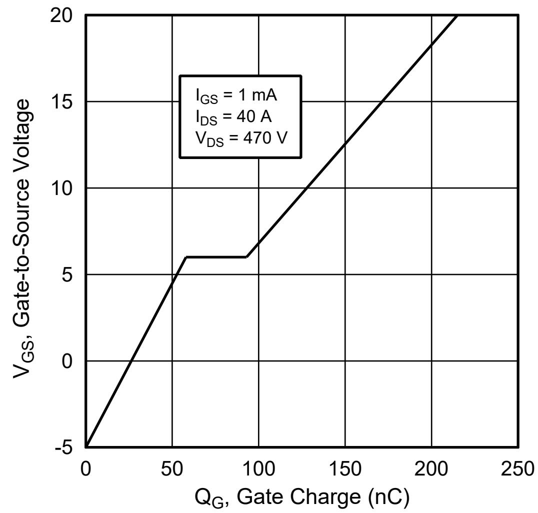


Figure 1-7. Capacitance vs. Drain-to-Source Voltage

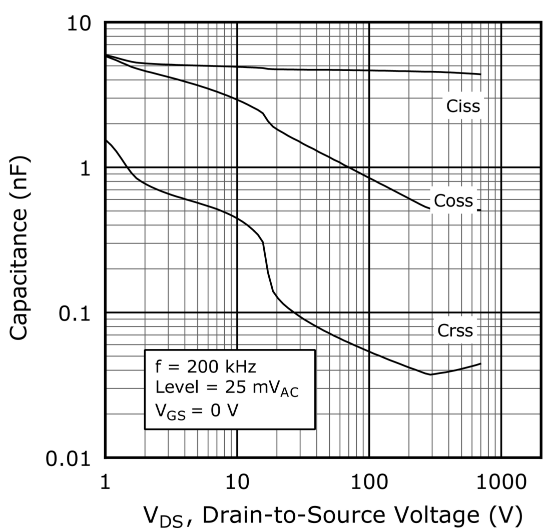


Figure 1-8. Output Charge vs. Drain-to-Source Voltage

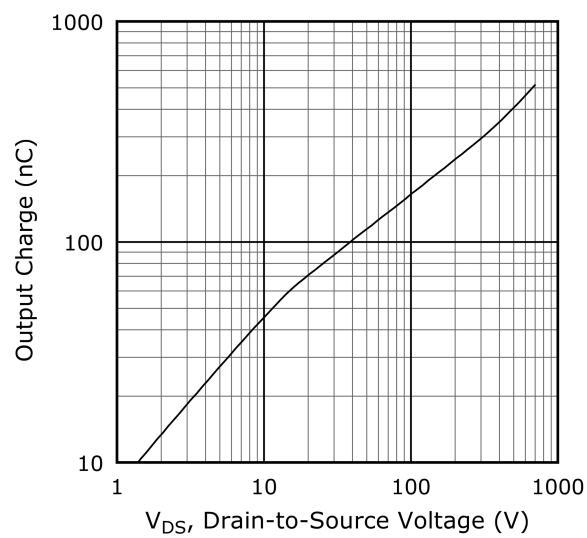


Figure 1-9. I_D vs. V_{DS} 3rd Quadrant Conduction

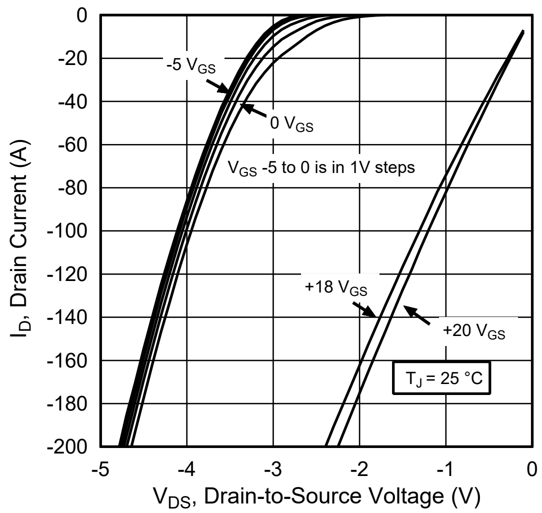


Figure 1-10. I_D vs. V_{DS} 3rd Quadrant Conduction

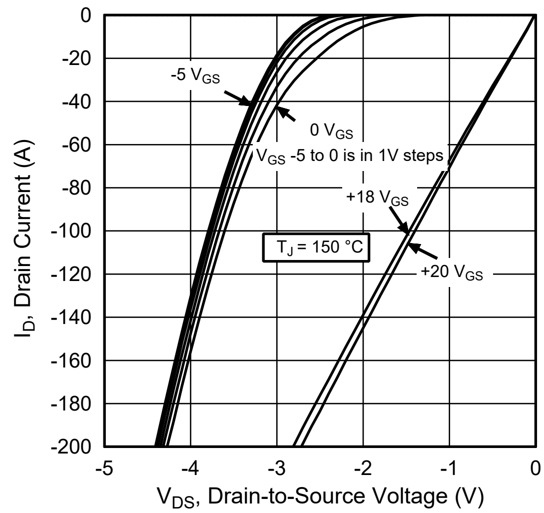


Figure 1-11. Switching Energy E_{on} vs. V_{DS} & I_D

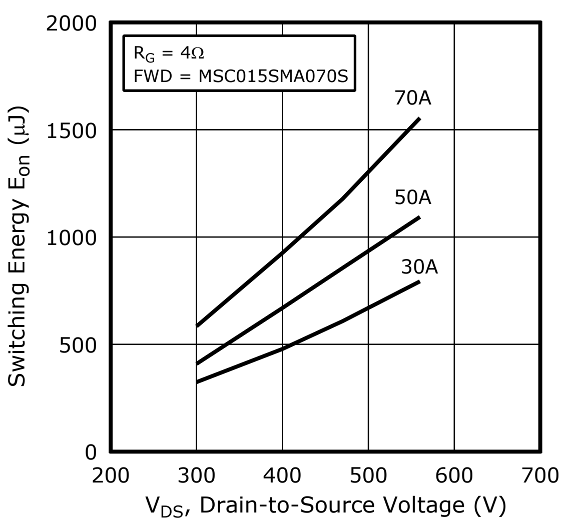


Figure 1-12. Switching Energy E_{off} vs. V_{DS} & I_D

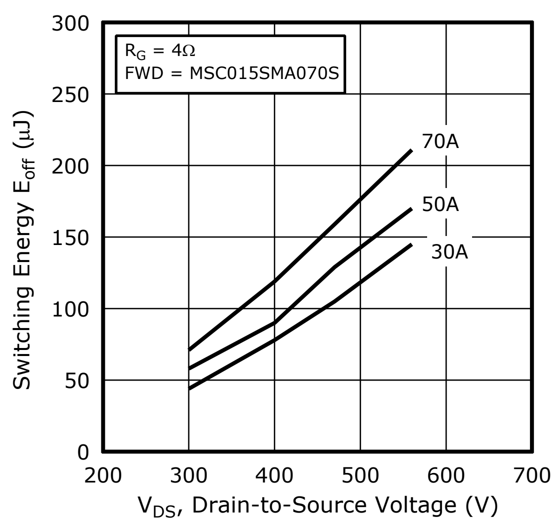


Figure 1-13. Switching Energy vs. R_G

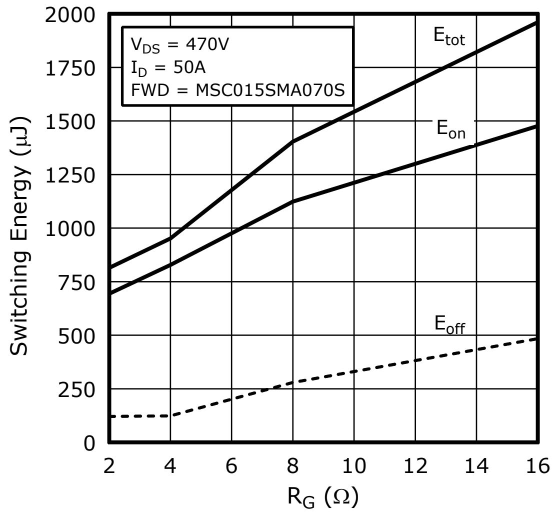


Figure 1-14. Switching Energy vs. Junction Temperature

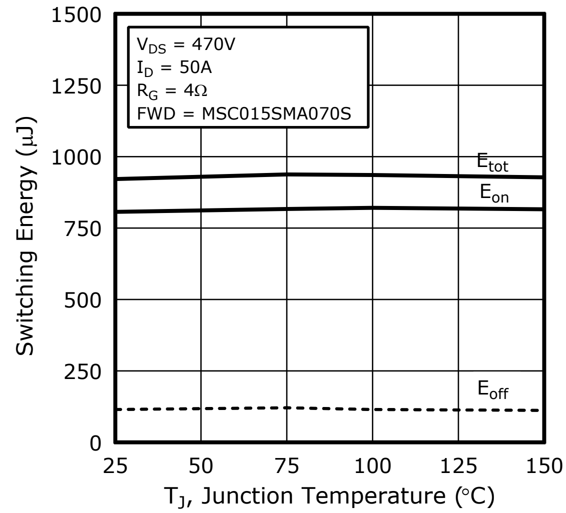


Figure 1-15. Threshold Voltage vs. Junction Temperature

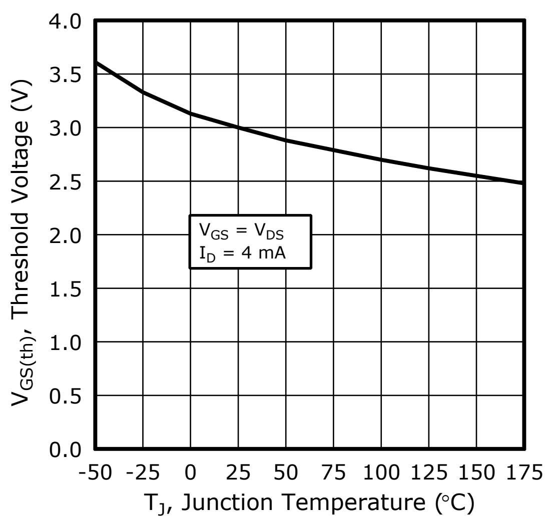


Figure 1-16. Forward Safe Operating Area

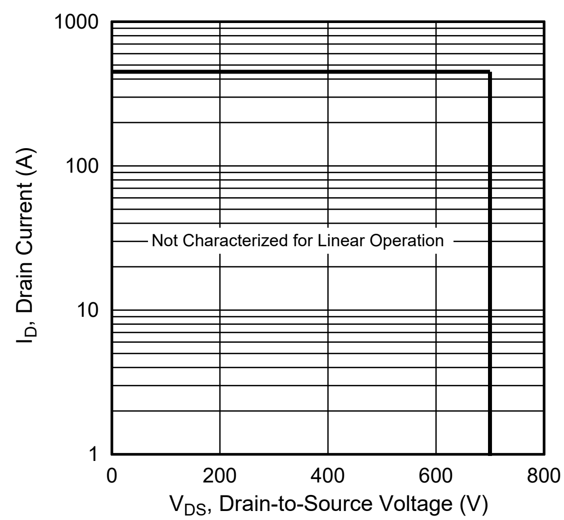
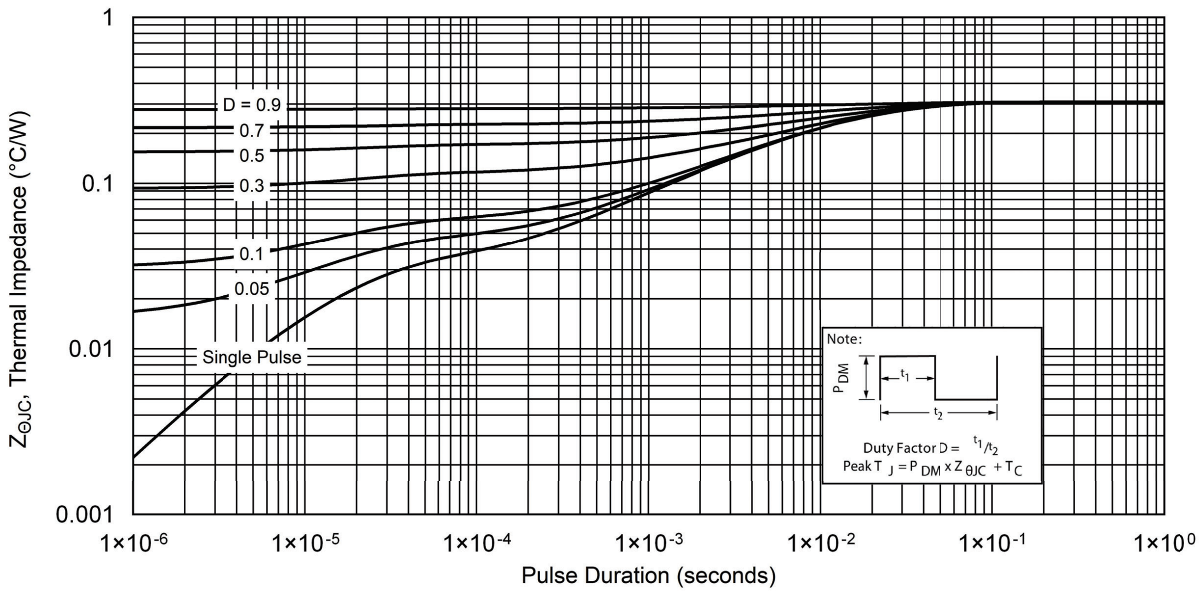
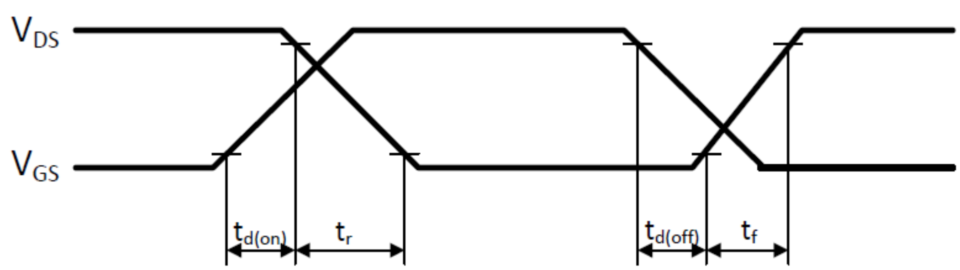


Figure 1-17. Maximum Transient Thermal Impedance



The following figure shows the switching waveform diagram of this device.

Figure 1-18. Switching Waveform



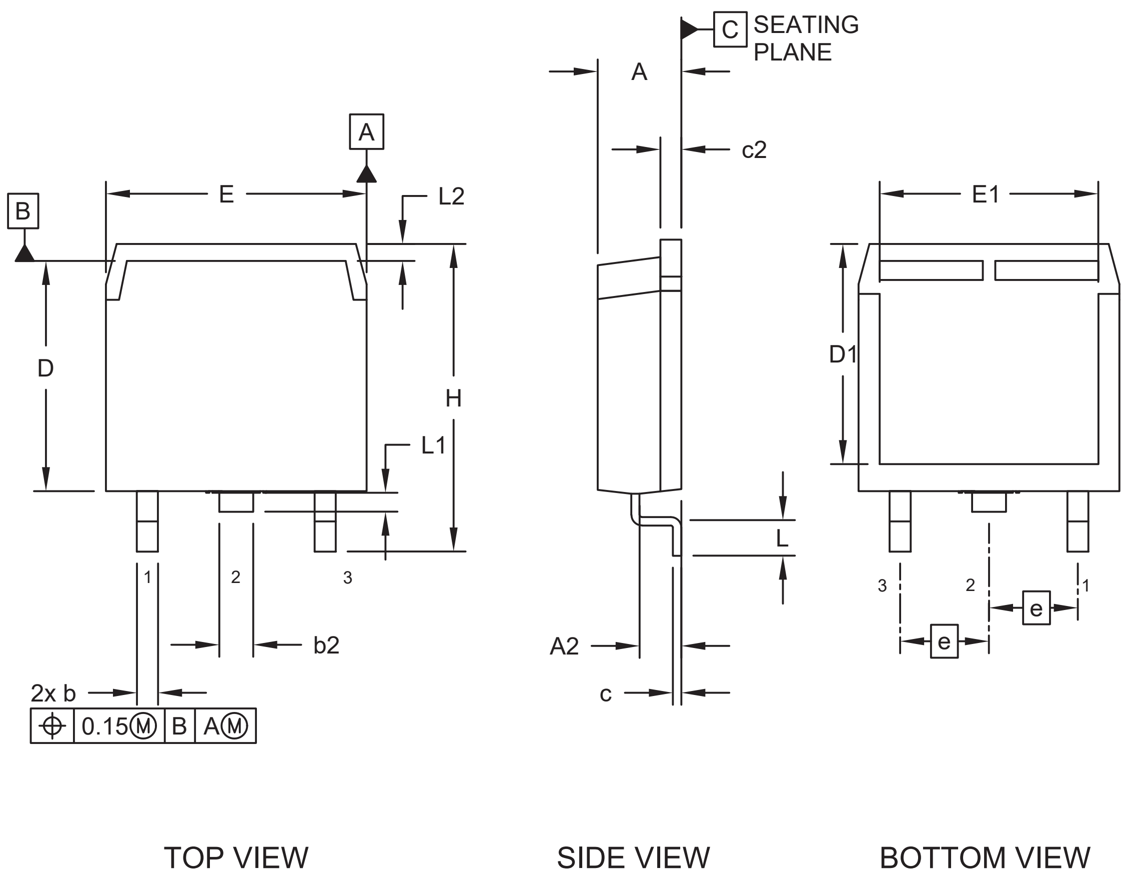
2. Package Specification

This section shows the package specification of this device.

2.1 Package Outline Drawing

The following figure illustrates the D3PAK (TO-268) package outline of this device.

Figure 2-1. Package Outline Drawing



The following table shows the D3PAK (TO-268) dimensions and should be used in conjunction with the package outline drawing.

Table 2-1. D3PAK (TO-268) Dimensions

Symbol	Description	Min. (mm)	Max. (mm)
N	Number of leads	3	
e	Pitch	5.46 BSC	
A	Overall height	4.90	5.11
A2	Seating plane to lead	2.69	2.90
b	Lead width	1.14	1.45
b2	Center lead width	1.96	2.21
H	Overall package length	18.69	19.10
c	Lead thickness	0.41	0.61
c2	Tab thickness	1.45	1.60

Symbol	Description	Min. (mm)	Max. (mm)
L	Foot length	2.39	2.69
L1	Center lead length	0.94	1.40
L2	Tab length	0.99	1.24
D	Molded body length	13.79	14.00
D1	Thermal pad length	12.40	12.70
E	Total width	15.85	16.21
E1	Thermal pad width	13.31	13.59

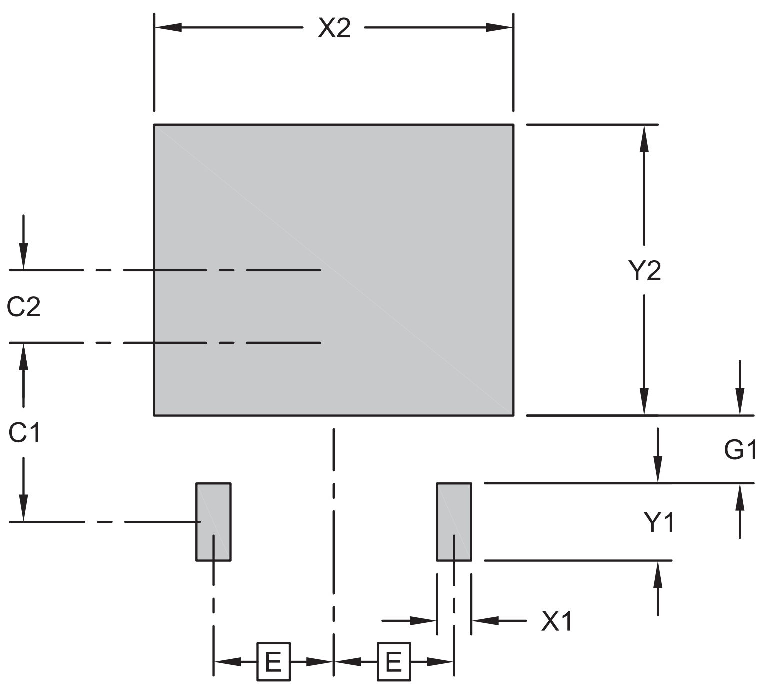
Note:
Dimensioning and tolerancing per ASME Y14.5M.

- BSC: Basic dimension. Theoretically exact value shown without tolerances.

2.2 Recommended Land Pattern

The following figure illustrates the recommended land pattern of this device.

Figure 2-2. Recommended Land Pattern



The following table shows the recommended land pattern dimensions.

Table 2-2. Recommended Land Pattern Dimensions

Symbol	Description	Min. (mm)	Nom. (mm)	Max. (mm)
E	Contact pitch	5.46 BSC		
X2	Center pad width	—	—	16.28
Y2	Center pad length	—	—	13.18
C1	Contact pad spacing	—	8.13	—
C2	Contact pad spacing	—	3.28	—
X1	Contact pad width (X2)	—	—	1.55

...........continued

Symbol	Description	Min. (mm)	Nom. (mm)	Max. (mm)
Y1	Contact pad length (X2)	—	—	3.48
G1	Contact pad to center pad (X2)	7.87	—	—

Notes:

- Dimensioning and tolerancing per ASME Y14.5M.
  - BSC: Basic dimension. Theoretically exact value shown without tolerances.
- For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process.

3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Table 3-1. Revision History

Revision	Date	Description
C	09/2024	The following changes are made in this revision of the document: • Updated value for I_{DM} in Table 1-1. • Updated Table 1-2. • Added $V_{GS(th)}$ (Max.) value in Table 1-3. • Updated I_D value (Test Conditions) in Table 1-4. • Added V_{SD} (Max.) value in Table 1-5. • Updated I_{SD} value (Test Conditions) in Table 1-5. • Updated Typical Performance Curves and Package Outline Drawing. • Added Recommended Land Pattern.
B	09/2023	The following changes are made in this revision of the document: • Replaced the lead temperature with reflow temperature in the Table 1-2. • Added Figure 1-8, Figure 1-9, Figure 1-10, and Figure 1-18. • Updated Figure 1-5 and Figure 1-16.
A	05/2023	Document migrated from Microsemi template to Microchip template; Assigned Microchip literature number DS-00004987A, which replaces the previous Microsemi literature number 050-7750.
Initial releases (Microsemi Revisions A and B)	08/2019 – 10/2019	Initial releases.

Microchip Information

The Microchip Website

Microchip provides online support via our website at www.microchip.com/. This website is used to make files and information easily available to customers. Some of the content available includes:

- **Product Support** – Data sheets and errata, application notes and sample programs, design resources, user's guides and hardware support documents, latest software releases and archived software
- **General Technical Support** – Frequently Asked Questions (FAQs), technical support requests, online discussion groups, Microchip design partner program member listing
- **Business of Microchip** – Product selector and ordering guides, latest Microchip press releases, listing of seminars and events, listings of Microchip sales offices, distributors and factory representatives

Product Change Notification Service

Microchip's product change notification service helps keep customers current on Microchip products. Subscribers will receive email notification whenever there are changes, updates, revisions or errata related to a specified product family or development tool of interest.

To register, go to www.microchip.com/pcn and follow the registration instructions.

Customer Support

Users of Microchip products can receive assistance through several channels:

- Distributor or Representative
- Local Sales Office
- Embedded Solutions Engineer (ESE)
- Technical Support

Customers should contact their distributor, representative or ESE for support. Local sales offices are also available to help customers. A listing of sales offices and locations is included in this document.

Technical support is available through the website at: www.microchip.com/support

Microchip Devices Code Protection Feature

Note the following details of the code protection feature on Microchip products:

- Microchip products meet the specifications contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is secure when used in the intended manner, within operating specifications, and under normal conditions.
- Microchip values and aggressively protects its intellectual property rights. Attempts to breach the code protection features of Microchip product is strictly prohibited and may violate the Digital Millennium Copyright Act.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of its code. Code protection does not mean that we are guaranteeing the product is "unbreakable". Code protection is constantly evolving. Microchip is committed to continuously improving the code protection features of our products.

Legal Notice

This publication and the information herein may be used only with Microchip products, including to design, test, and integrate Microchip products with your application. Use of this information in any other manner violates these terms. Information regarding device applications is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. Contact your local Microchip sales office for additional support or, obtain additional support at www.microchip.com/en-us/support/design-help/client-support-services.

Trademarks

ISBN: 978-1-6683-0177-7

Quality Management System

For information regarding Microchip's Quality Management Systems, please visit www.microchip.com/quality.

Worldwide Sales and Service

AMERICAS

Corporate Office
2355 West Chandler Blvd.
Chandler, AZ 85224-6199
Tel: 480-792-7200
Fax: 480-792-7277
Technical Support:
www.microchip.com/support
Web Address:
www.microchip.com

Atlanta
Duluth, GA
Tel: 678-957-9614
Fax: 678-957-1455

Austin, TX
Tel: 512-257-3370

Boston
Westborough, MA
Tel: 774-760-0087
Fax: 774-760-0088

Chicago
Itasca, IL
Tel: 630-285-0071
Fax: 630-285-0075

Dallas
Addison, TX
Tel: 972-818-7423
Fax: 972-818-2924

Detroit
Novi, MI
Tel: 248-848-4000

Houston, TX
Tel: 281-894-5983

Indianapolis
Noblesville, IN
Tel: 317-773-8323
Fax: 317-773-5453
Tel: 317-536-2380

Los Angeles
Mission Viejo, CA
Tel: 949-462-9523
Fax: 949-462-9608
Tel: 951-273-7800

Raleigh, NC
Tel: 919-844-7510

New York, NY
Tel: 631-435-6000

San Jose, CA
Tel: 408-735-9110
Tel: 408-436-4270

Canada - Toronto
Tel: 905-695-1980
Fax: 905-695-2078

ASIA/PACIFIC

Australia - Sydney
Tel: 61-2-9868-6733

China - Beijing
Tel: 86-10-8569-7000

China - Chengdu
Tel: 86-28-8665-5511

China - Chongqing
Tel: 86-23-8980-9588

China - Dongguan
Tel: 86-769-8702-9880

China - Guangzhou
Tel: 86-20-8755-8029

China - Hangzhou
Tel: 86-571-8792-8115

China - Hong Kong SAR
Tel: 852-2943-5100

China - Nanjing
Tel: 86-25-8473-2460

China - Qingdao
Tel: 86-532-8502-7355

China - Shanghai
Tel: 86-21-3326-8000

China - Shenyang
Tel: 86-24-2334-2829

China - Shenzhen
Tel: 86-755-8864-2200

China - Suzhou
Tel: 86-186-6233-1526

China - Wuhan
Tel: 86-27-5980-5300

China - Xian
Tel: 86-29-8833-7252

China - Xiamen
Tel: 86-592-2388138

China - Zhuhai
Tel: 86-756-3210040

ASIA/PACIFIC

India - Bangalore
Tel: 91-80-3090-4444

India - New Delhi
Tel: 91-11-4160-8631

India - Pune
Tel: 91-20-4121-0141

Japan - Osaka
Tel: 81-6-6152-7160

Japan - Tokyo
Tel: 81-3-6880- 3770

Korea - Daegu
Tel: 82-53-744-4301

Korea - Seoul
Tel: 82-2-554-7200

Malaysia - Kuala Lumpur
Tel: 60-3-7651-7906

Malaysia - Penang
Tel: 60-4-227-8870

Philippines - Manila
Tel: 63-2-634-9065

Singapore
Tel: 65-6334-8870

Taiwan - Hsin Chu
Tel: 886-3-577-8366

Taiwan - Kaohsiung
Tel: 886-7-213-7830

Taiwan - Taipei
Tel: 886-2-2508-8600

Thailand - Bangkok
Tel: 66-2-694-1351

Vietnam - Ho Chi Minh
Tel: 84-28-5448-2100

EUROPE

Austria - Wels
Tel: 43-7242-2244-39
Fax: 43-7242-2244-393

Denmark - Copenhagen
Tel: 45-4485-5910
Fax: 45-4485-2829

Finland - Espoo
Tel: 358-9-4520-820

France - Paris
Tel: 33-1-69-53-63-20
Fax: 33-1-69-30-90-79

Germany - Garching
Tel: 49-8931-9700

Germany - Haan
Tel: 49-2129-3766400

Germany - Heilbronn
Tel: 49-7131-72400

Germany - Karlsruhe
Tel: 49-721-625370

Germany - Munich
Tel: 49-89-627-144-0
Fax: 49-89-627-144-44

Germany - Rosenheim
Tel: 49-8031-354-560

Israel - Hod Hasharon
Tel: 972-9-775-5100

Italy - Milan
Tel: 39-0331-742611
Fax: 39-0331-466781

Italy - Padova
Tel: 39-049-7625286

Netherlands - Drunen
Tel: 31-416-690399
Fax: 31-416-690340

Norway - Trondheim
Tel: 47-72884388

Poland - Warsaw
Tel: 48-22-3325737

Romania - Bucharest
Tel: 40-21-407-87-50

Spain - Madrid
Tel: 34-91-708-08-90
Fax: 34-91-708-08-91

Sweden - Gothenberg
Tel: 46-31-704-60-40

Sweden - Stockholm
Tel: 46-8-5090-4654

UK - Wokingham
Tel: 44-118-921-5800
Fax: 44-118-921-5820